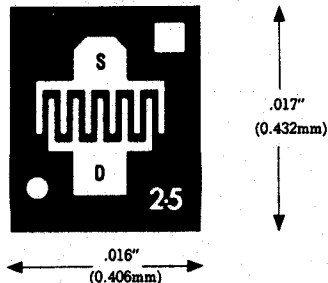


CHIP NUMBER

**FN3.6**



Die Size: .16 x .17 (mils)  
0.406 x 0.432(mm)  
3 x 3 (mils)  
Pad Size: 0.076 x 0.076(mm)  
GATE-SUBSTRATE

**CONTACT METALLIZATION**

Top Contact: > 12,000  
Å Aluminum

Backside Contact: 3,000 Å Gold

**ASSEMBLY RECOMMENDATIONS**

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

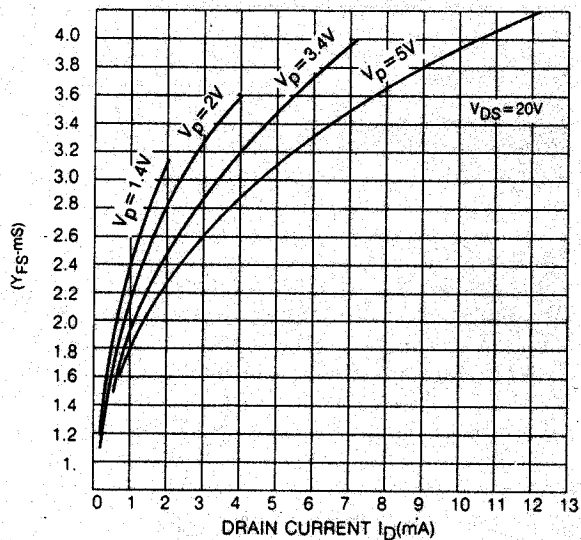
**TYPICAL ELECTRICAL CHARACTERISTICS**

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-30	-50	-70	V	$V_{DS} = 0, I_G = 1\mu A$
$I_{DSS}$	0.5	8.0	20	mA	$V_{DS} = 15V, V_{GS} = 0$
$g_{fs}$	1.5	4.0	6.0	mmho	$V_{DS} = 15V, V_{GS} = 0$
$I_{GSS}$		25	100	pA	$V_{GS} = -30V, V_{DS} = 0$
$r_{DS}$	150	200	600	$\Omega$	$V_{DS} = 100mV, V_{GS} = 0$
$V_{GS(off)}$	-1.0	-3.0	8.0	V	$V_{DS} = 15V, I_D = 1nA$
$C_{rss}$	1.2	2.0	3.0	pF	$V_{DS} = 15V, V_{GS} = 0, f = 1MHz$
$C_{iss}$		4.5	6.0	pF	$V_{DS} = 15V, V_{GS} = 0, f = 1MHz$

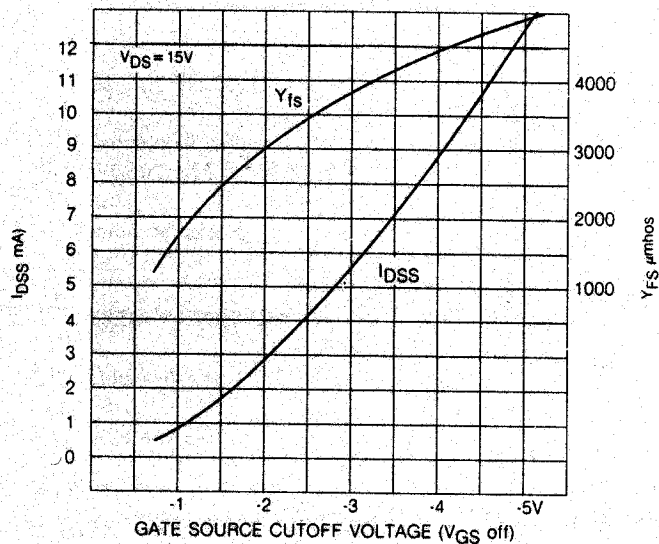
TYPICAL DEVICE TYPES: 2N3821 - 2N3824, 2N3921 - 2N3922, 2N5545 - 2N5547

### CHIP TYPE FN3.6

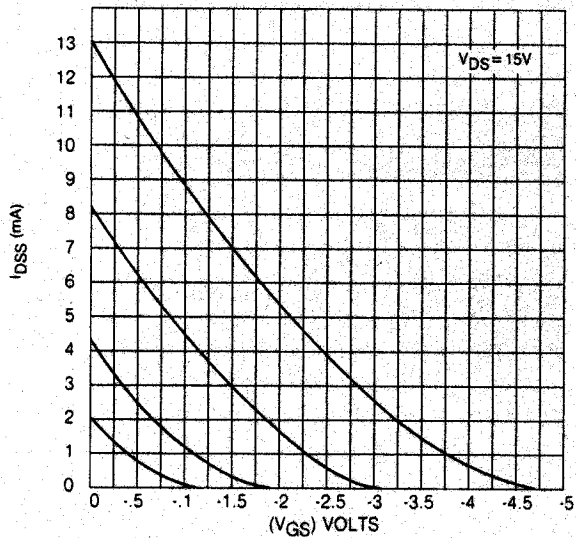
FORWARD TRANSADMITTANCE  
VS. OPERATING DRAIN CURRENT



FORWARD TRANSADMITTANCE VS



TRANSFER CHARACTERISTICS



OUTPUT CHARACTERISTICS

